TOSHIBA 2SB1018A

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2 S B 1 O 1 8 A

HIGH CURRENT SWITCHING APPLICATIONS

POWER AMPLIFIER APPLICATIONS

High Collector Current : $I_C = -7 A$

Low Collector Saturation Voltage

 $: V_{CE (sat)} = -0.5 V (Max.) (I_{C} = -4 A)$

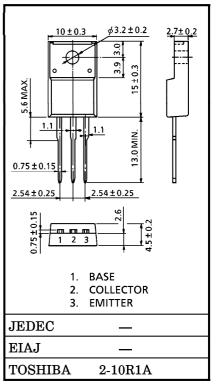
Complementary to 2SD1411A

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	v_{CBO}	-100	V	
Collector-Emitter Voltage	v_{CEO}	-80	V	
Emitter-Base Voltage	$v_{ m EBO}$	-5	V	
Collector Current	$I_{\mathbf{C}}$	- 7	A	
Base Current	$I_{\mathbf{B}}$	-1	A	
Collector Power Ta =	25°C PC	2.0	W	
Dissipation Tc =	: 25°C	30		
Junction Temperature	$T_{ m j}$	150	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$ m T_{stg}$	-55~150	°C	

INDUSTRIAL APPLICATIONS

Unit in mm



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARA	ACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cu	ıt-off Current	I_{CBO}	$V_{CB} = -100 \text{ V}, I_{E} = 0$	_	_	-5	μ A
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$		_	-5	μ A
Collector-En Breakdown		V (BR) CEO	$I_{\rm C} = -50 {\rm mA}, I_{\rm B} = 0$	-80	_	_	V
DC Current Gain		hFE (1) (Note)	$V_{CE} = -1 V, I_{C} = -1 A$	70	_	240	
		h _{FE} (2)	$V_{CE} = -1 V, I_{C} = -4 A$	30	_	_	
Saturation	Collector-Emitter	V _{CE} (sat)	$I_C = -4 A, I_B = -0.4 A$	_	-0.3	-0.5	v
Voltage	Base-Emitter	V _{BE} (sat)	$I_C = -4 A, I_B = -0.4 A$	_	-0.9	-1.4] v
Transition Frequency		${ m f_T}$	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	_	10	_	MHz
Collector Output Capacitance		Cob	$V_{CB} = -10 V, I_{E} = 0,$ f = 1 MHz		250	_	pF
Switching Time	Turn-on Time	t _{on}	$\begin{array}{c c} I_{B2} & \text{OUTPUT} \\ \hline 20 \ \mu\text{s} & \text{INPUT} & & \\ \hline I_{B2} & I_{B1} & & \\ \hline \end{array}$		0.4	_	
	Storage Time	$\mathbf{t}_{ ext{stg}}$	I_{B1} I_{B2} I_{B1} $V_{CC} = -30 \text{ V}$	_	2.5	_	μ s
	Fall Time	t_f	$-I_{B1} = I_{B2} = 0.3 \text{ A},$ DUTY CYCLE $\leq 1\%$		0.5	_	

(Note) : $h_{\mbox{FE (1)}}$ Classification O : $70{\sim}140$, Y : $120{\sim}240$

